

1SS277WT

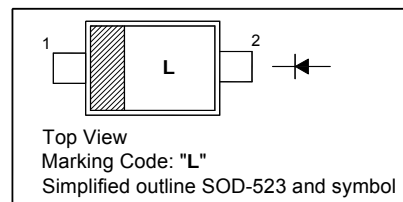
BAND SWITCHING DIODE

Applications

- Low loss band switching in VHF television tuners
- Surface mount band switching circuits

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

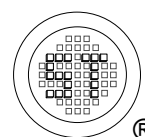


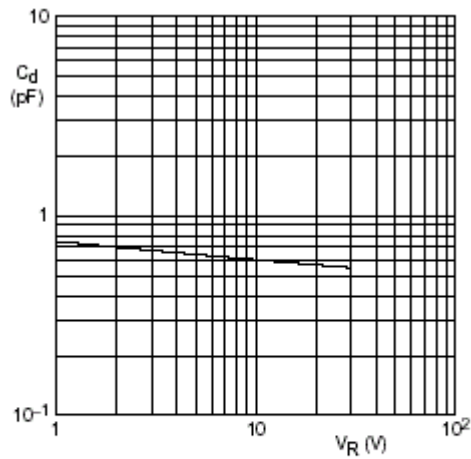
Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Continuous Forward Current	I_F	100	mA
Power Dissipation ($T_S = 90\text{ }^{\circ}\text{C}$)	P_{tot}	715	mW
Junction Temperature	T_J	- 65 to + 175	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

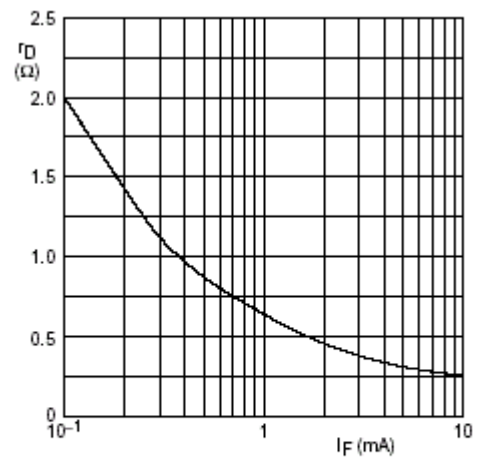
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	-	1	V
Reverse Voltage at $I_R = 10\text{ }\mu\text{A}$	V_R	35	-	V
Reverse Current at $V_R = 25\text{ V}$	I_R	-	50	nA
Diode Forward Resistance at $I_F = 2\text{ mA}$, $f = 100\text{ MHz}$	r_f	-	0.7	Ω
Capacitance at $f = 1\text{ MHz}$, $V_R = 6\text{ V}$	C_d	-	1.2	pF





$f = 1 \text{ MHz}; T_j = 25^\circ\text{C}$.

Fig. 1 Diode capacitance as a function of reverse voltage; typical values.



$f = 100 \text{ MHz}; T_j = 25^\circ\text{C}$.

Fig. 2 Diode forward resistance as a function of forward current; typical values.

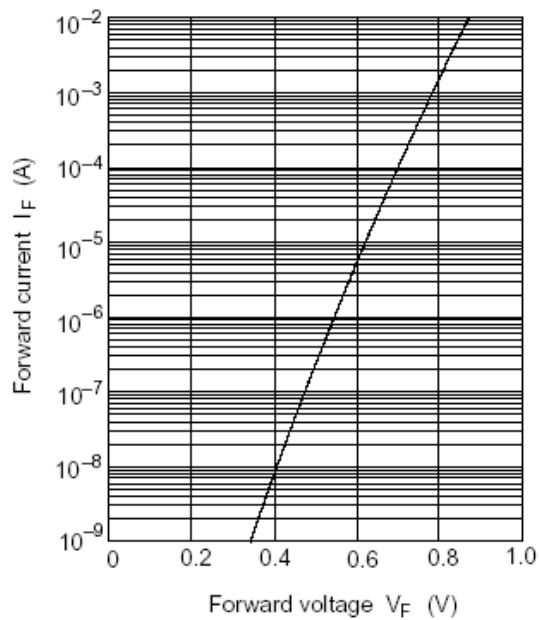


Fig. 3 Forward current Vs. Forward voltage

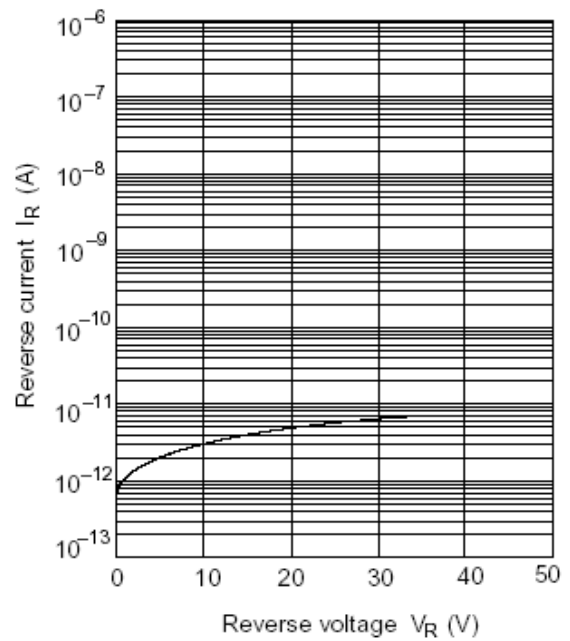
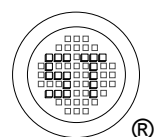


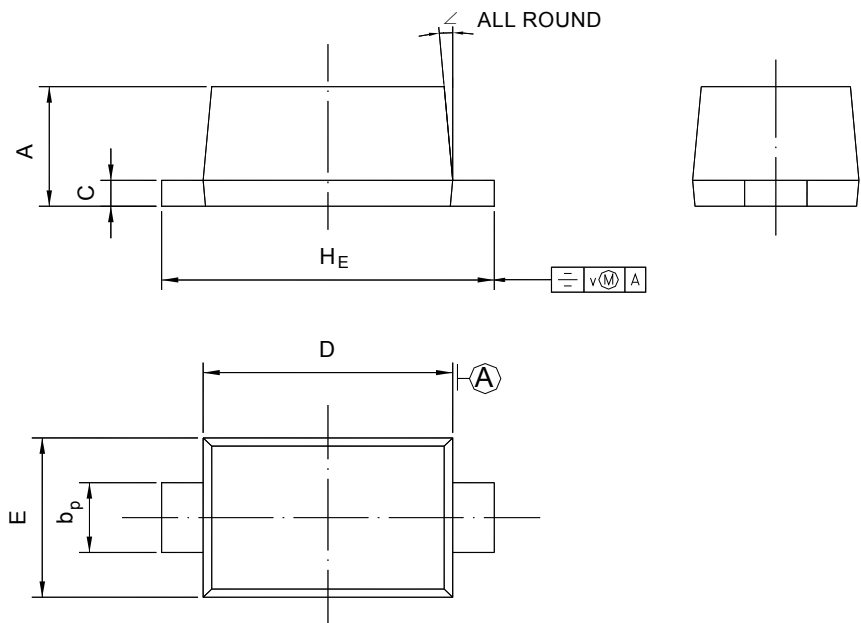
Fig. 4 Reverse current Vs. Reverse voltage



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

